



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

2823  
# 466  
11/18/02  
11/18/02

In re application of

JOZEF D. MITROS

Serial No. 10/020,034 (11-32932)

Filed December 2, 2001

For: METHOD FOR FABRICATING LOW CHC  
DEGRADATION MOSFET TRANSISTORS

Art Unit 2823

Examiner Long Pham

Commissioner for Patents  
Washington, D. C. 20231

Sir:

**AMENDMENT UNDER 37 C.F.R. 1.116**

In response to the Office action dated September 18, 2002, please amend the  
above identified application as follows:

**In the claims:**

Amend claim 8 as follows:

8. (Amended) The method of claim 1, wherein the first and third transistor  
devices comprise NMOS transistors, wherein the second and fourth transistor devices  
comprise PMOS transistors, and wherein implanting a portion of the third transistor  
region [using the fourth implantation process] comprises implanting boron in a portion of  
the fourth transistor region.